FIG. 1A

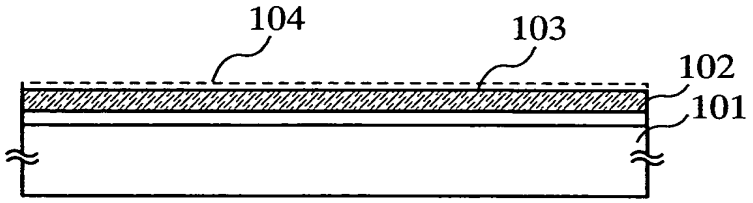


FIG. 1B

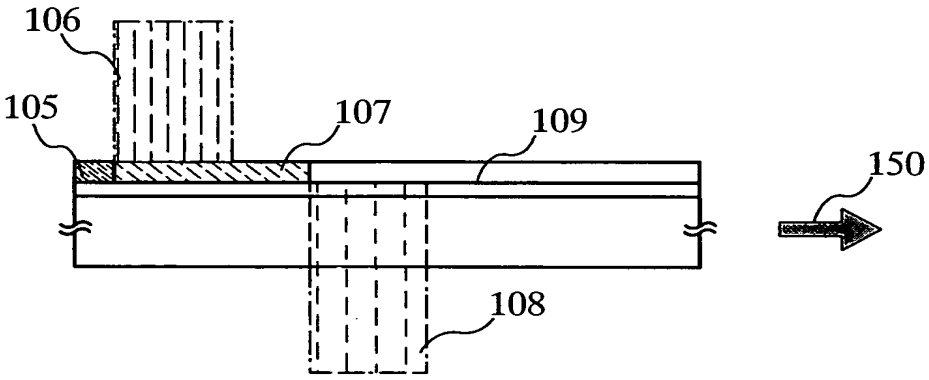


FIG. 1C

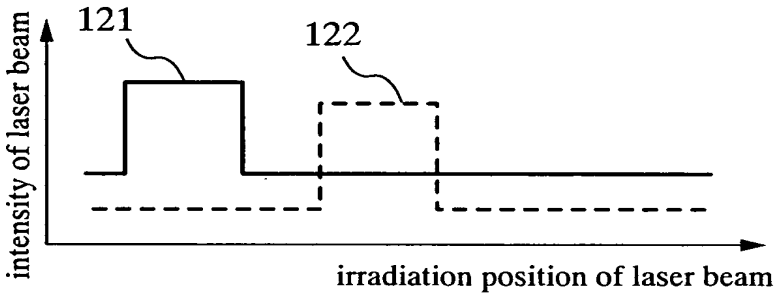


FIG. 1D

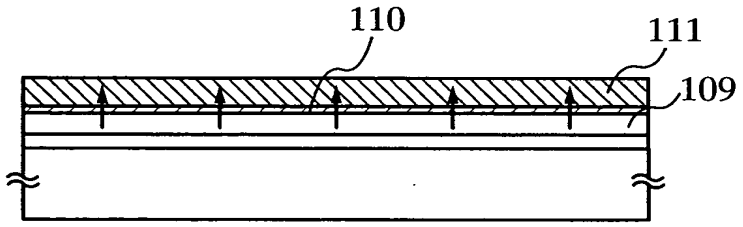
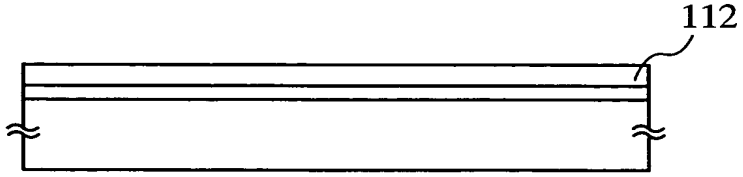


FIG. 1E



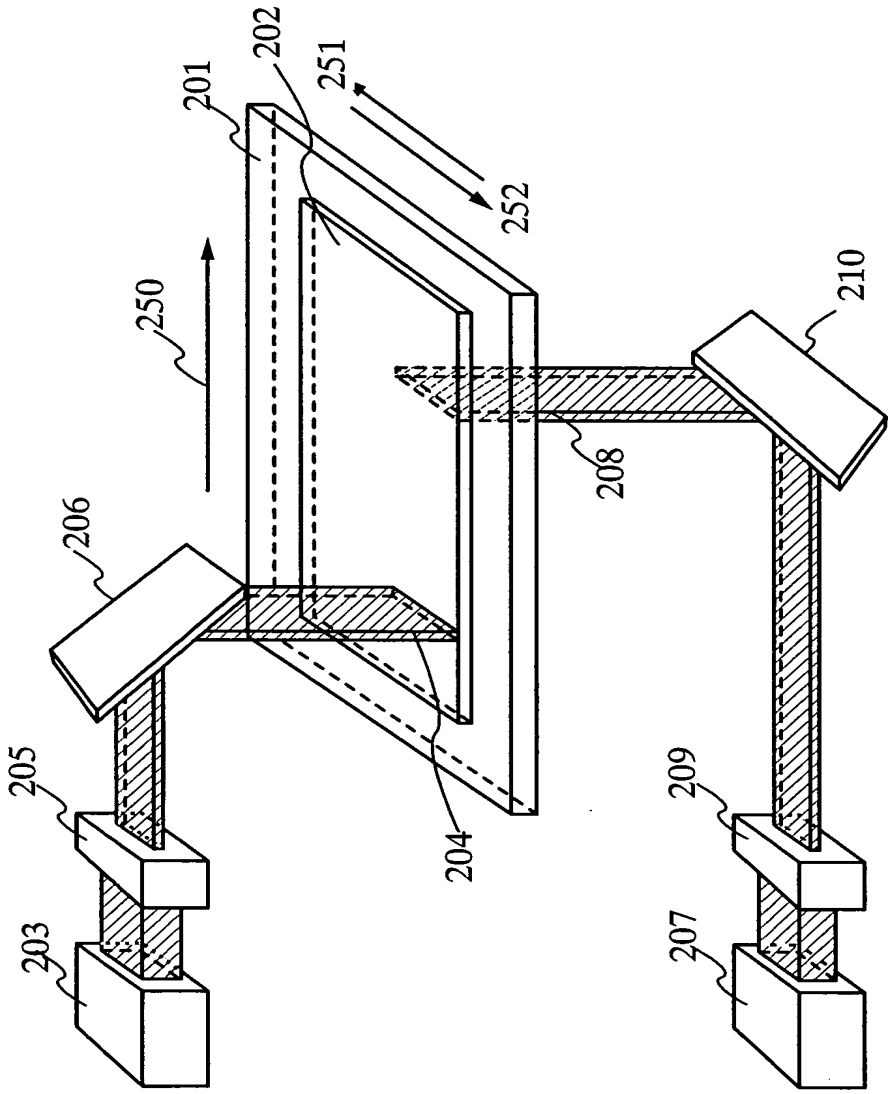


FIG. 2

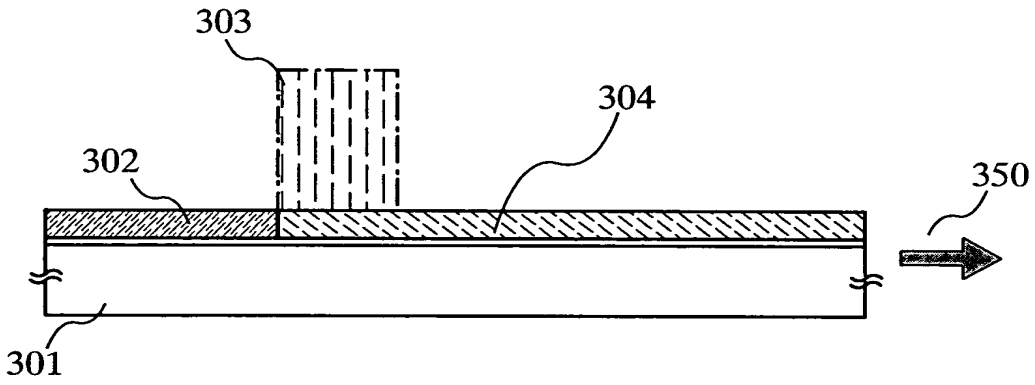


FIG. 3A

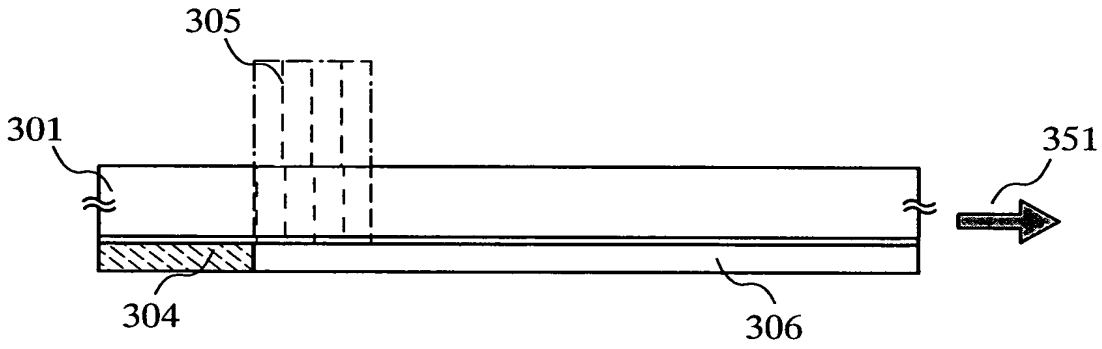


FIG. 3B

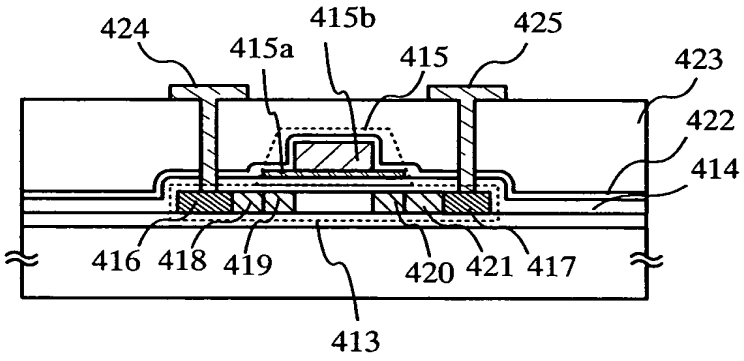


FIG. 4

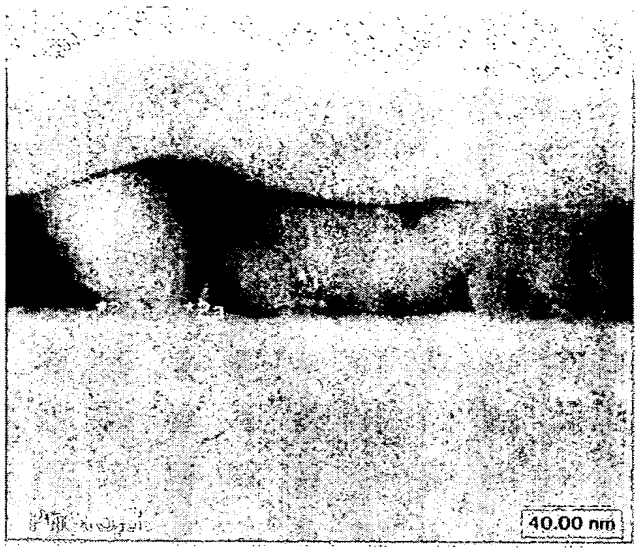


FIG. 5A

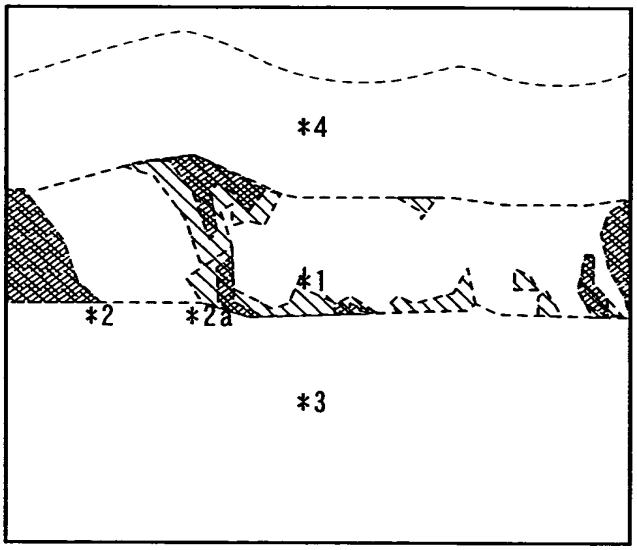
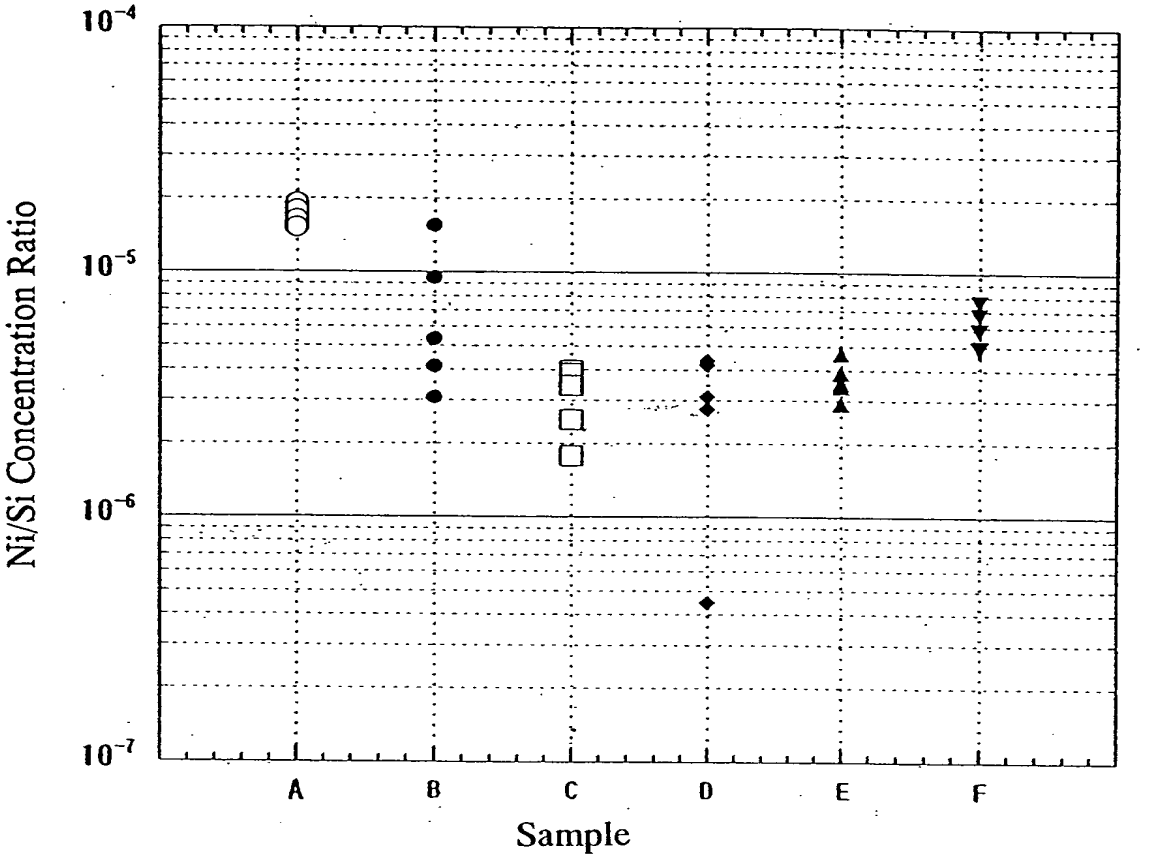


FIG. 5B



○ A; solid phase epitaxy with element

● B; solid phase epitaxy with element + laser annealing (XeCl (485mJcm^{-2}))

□ C; solid phase epitaxy with element + laser annealing (XeCl (485mJcm^{-2})+YAG (100mJcm^{-2}))

◆ D; solid phase epitaxy with element + laser annealing (XeCl (485mJcm^{-2})+YAG (125mJcm^{-2}))

▲ E; solid phase epitaxy with element + laser annealing (XeCl (485mJcm^{-2})+YAG (150mJcm^{-2}))

▼ F; solid phase epitaxy with element + laser annealing (XeCl (485mJcm^{-2})+YAG (200mJcm^{-2}))

FIG. 6

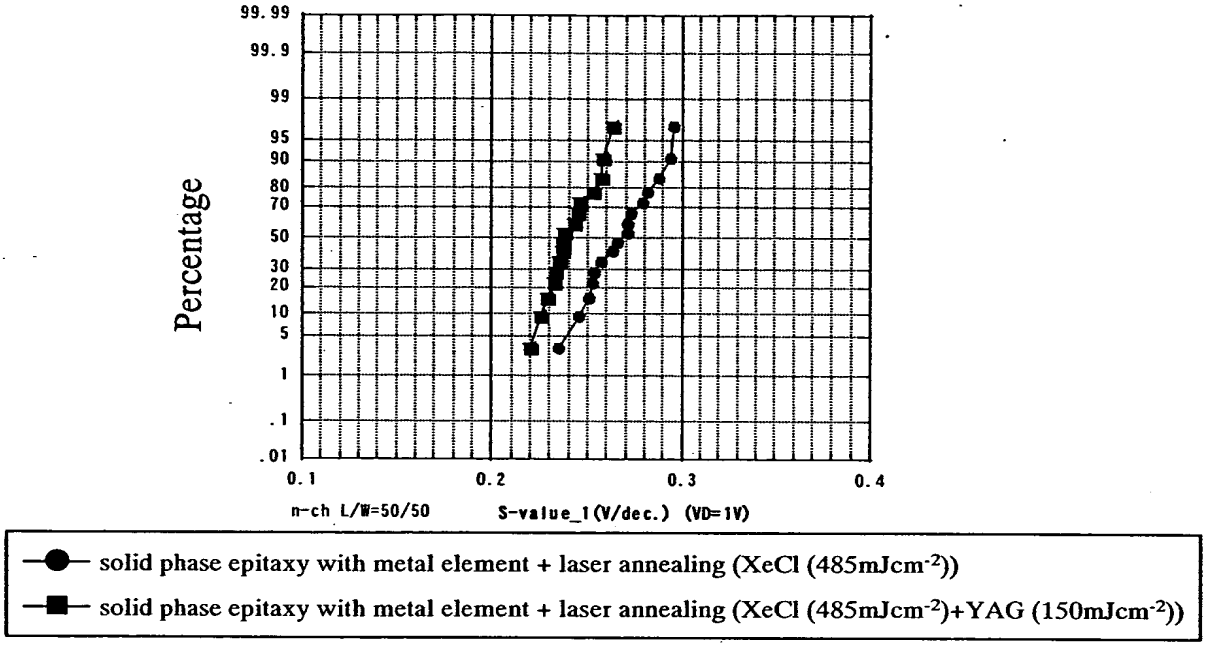

99.99
99.9
99
95
90
80
70
50
30
20
10
5
1
.1
.01
Percentage
0.1
0.2
0.3
0.4
n-ch L/W=50/50
S-value_1(V/dec.) (VD=1V)
solid phase epitaxy with metal element + laser annealing (XeCl (485mJcm-2))
solid phase epitaxy with metal element + laser annealing (XeCl (485mJcm-2)+YAG (150mJcm-2))

FIG. 7A

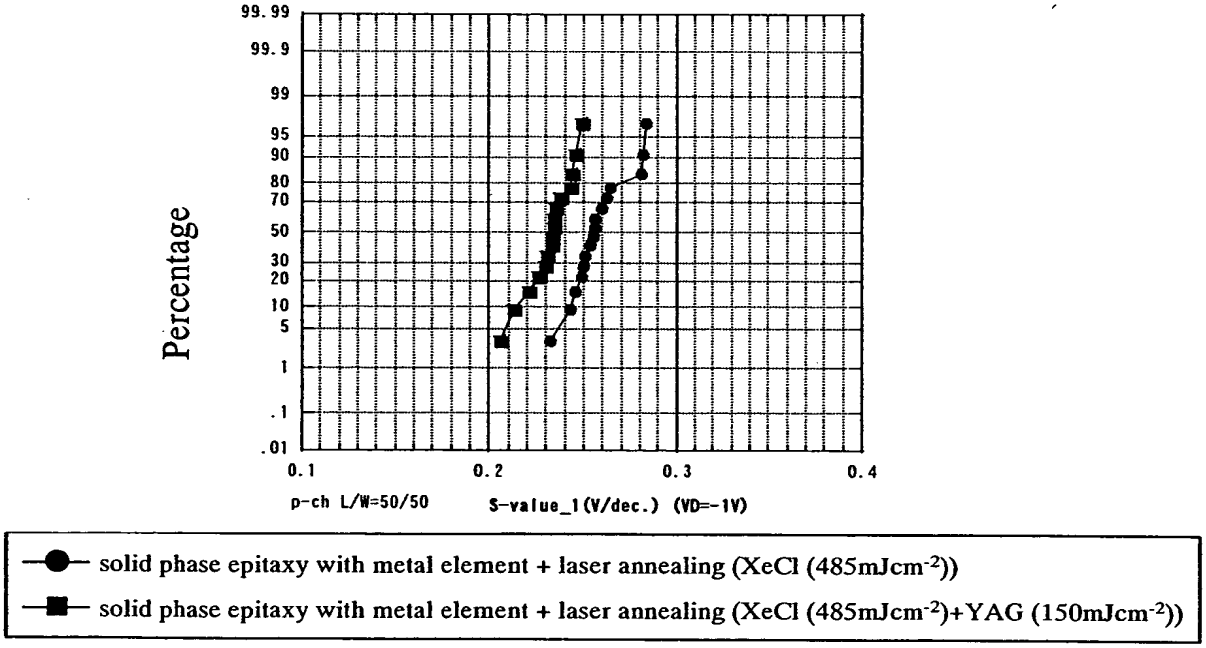

99.99
99.9
99
95
90
80
70
50
30
20
10
5
1
.1
.01
Percentage
0.1
0.2
0.3
0.4
p-ch L/W=50/50
S-value_1(V/dec.) (VD=-1V)
solid phase epitaxy with metal element + laser annealing (XeCl (485mJcm-2))
solid phase epitaxy with metal element + laser annealing (XeCl (485mJcm-2)+YAG (150mJcm-2))

FIG. 7B

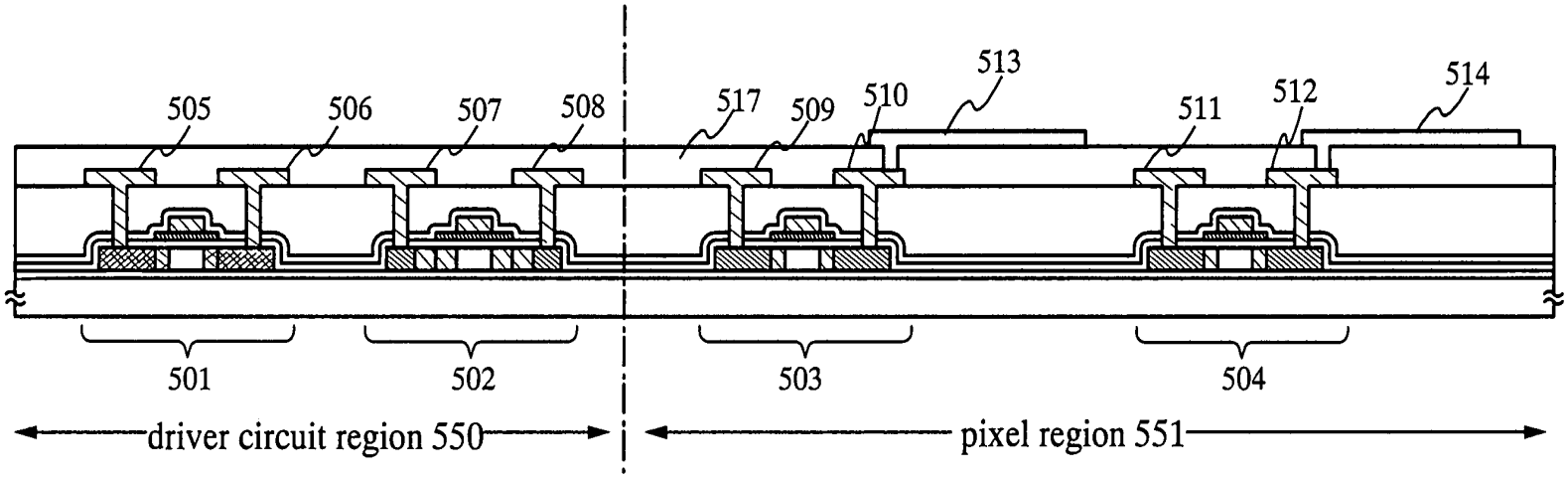

505
506
507
508
517
509
510
513
511
512
514
501
502
503
504
driver circuit region 550
pixel region 551

FIG. 8

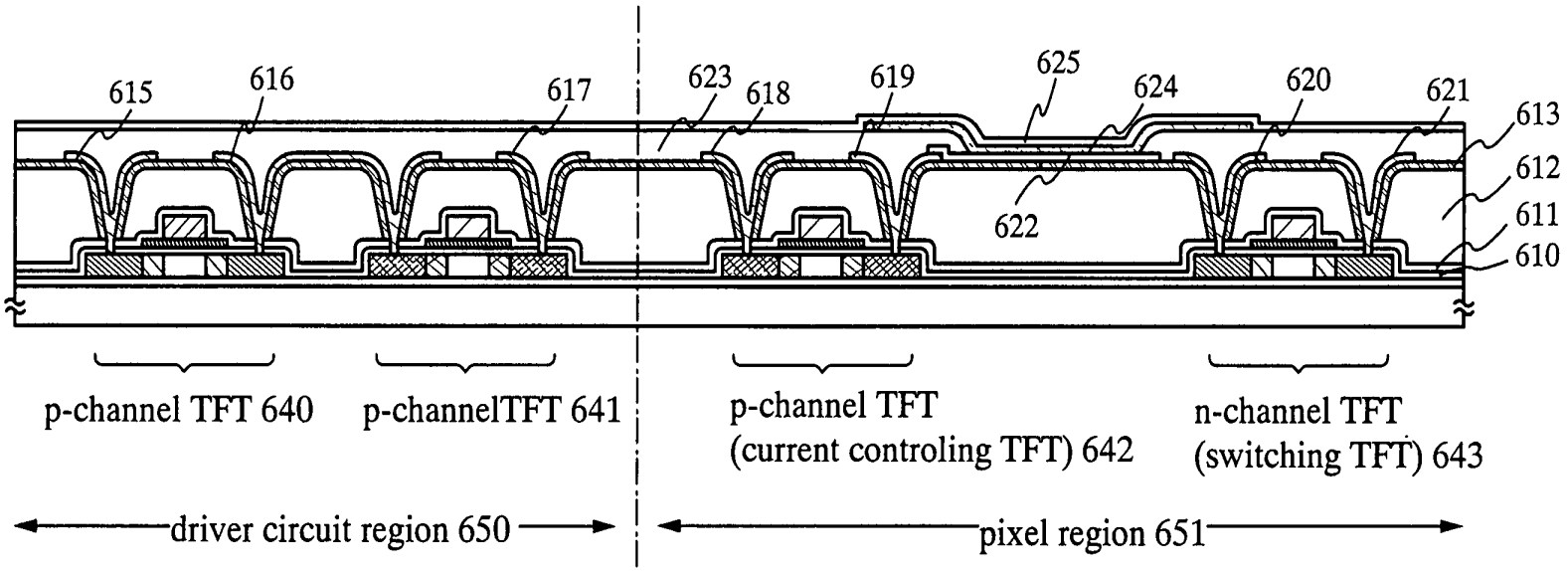

615
616
617
623
618
619
625
624
620
621
613
612
611
610
622
p-channel TFT 640
p-channelTFT 641
p-channel TFT
(current controling TFT) 642
n-channel TFT
(switching TFT) 643
driver circuit region 650
pixel region 651

FIG. 9

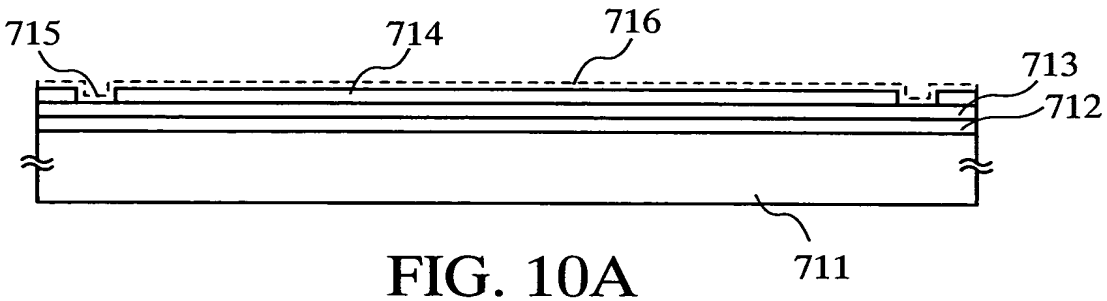


FIG. 10A

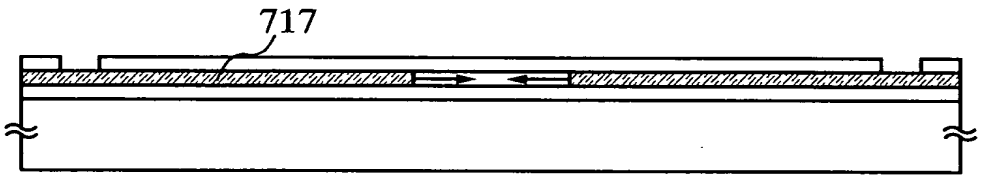


FIG. 10B

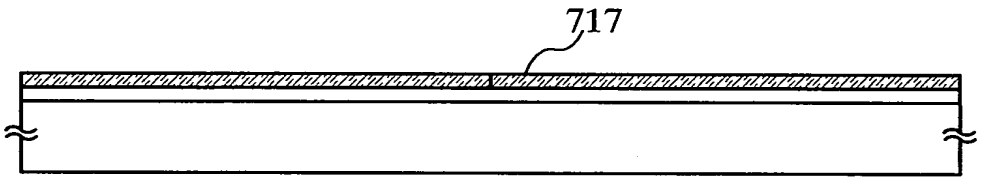


FIG. 10C

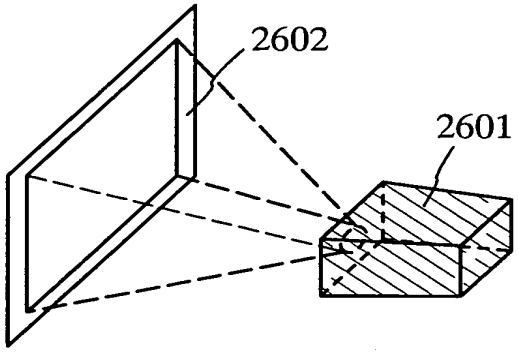


FIG. 11A

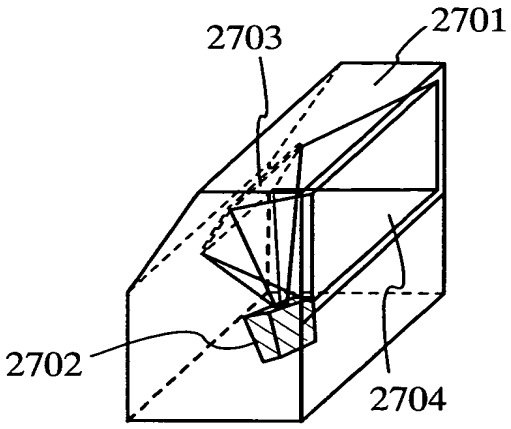


FIG. 11B

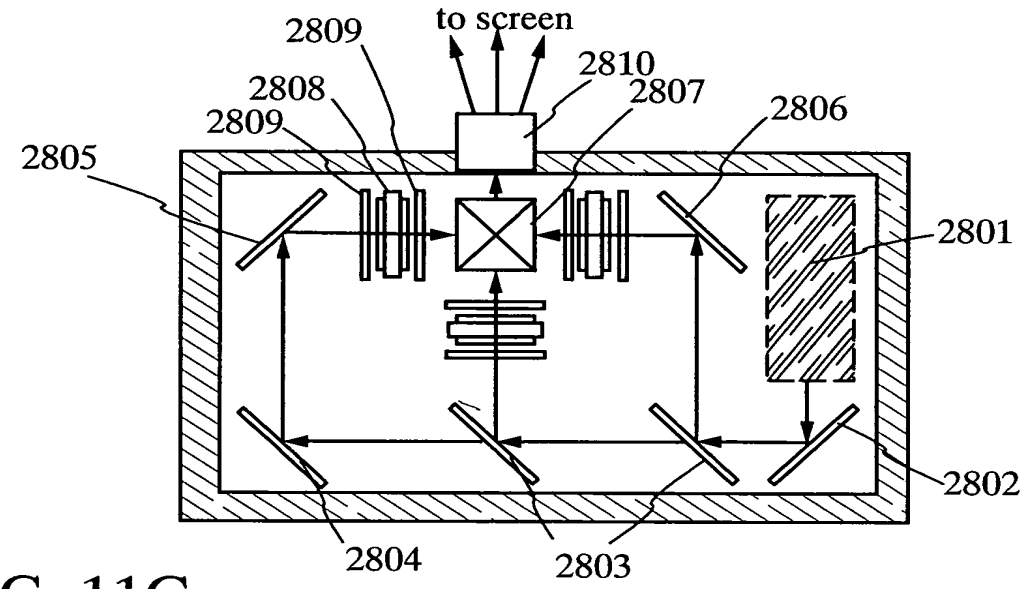


FIG. 11C

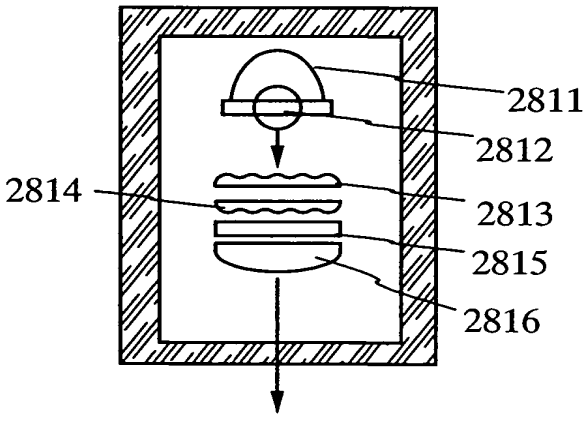


FIG. 11D